GeneSiC™ SEMICONDUCTOR

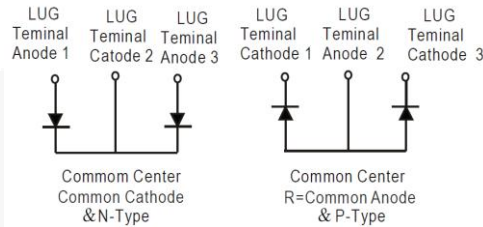## Silicon Power Schottky Diode

V_{RRM} = 20 V - 40 V

$I_{F(AV)}$ = 400 A

Features

- High Surge Capability
- Types from 20 V to 40 V V_{RRM}
- Isolation Type Package
- Electrically Isolated Base Plate
- Not ESD Sensitive

Three Tower Package

LUG Terminal Anode 1 — LUG Terminal Catode 2 — LUG Terminal Anode 3
Commom Center Common Cathode & N-Type

LUG Terminal Cathode 1 — LUG Terminal Anode 2 — LUG Terminal Cathode 3
Common Center R=Common Anode & P-Type

RoHS COMPLIANT

REACH COMPLIANCE

Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRT40020(R)	MBRT40030(R)	MBRT40035(R)	MBRT40040(R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Operating temperature	T_j		-55 to 150	-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T_{stg}		-55 to 150	-55 to 150	-55 to 150	-55 to 150	°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MBRT40020(R)	MBRT40030(R)	MBRT40035(R)	MBRT40040(R)	Unit
Average forward current (per pkg)	$I_{F(AV)}$	T_C =125 °C	400	400	400	400	A
Peak forward surge current (per leg)	I_{FSM}	t_p = 8.3 ms, half sine	3000	3000	3000	3000	A
Maximum instantaneous forward voltage (per leg)	V_F	I_{FM} = 200 A, T_j = 25 °C	0.70	0.70	0.70	0.70	V
Maximum Instantaneous reverse current at rated DC blocking voltage (per leg)	I_R	T_j = 25 °C	1	1	1	1	mA
		T_j = 100 °C	10	10	10	10	
		T_j = 150 °C	50	50	50	50	
Thermal characteristics							
Maximum thermal resistance, junction - case (per leg)	$R_{\Theta JC}$		0.35	0.35	0.35	0.35	°C/W

GeneSiC™
SEMICONDUCTOR

Figure.1-Typical Forward Characteristics

$T_J = 25°C$

MBRT40020(R)
MBRT40030(R)
MBRT40035(R)
MBRT40040(R)
MBRT40045(R)

MBRT40060(R)

MBRT40080(R)
MBRT400100(R)

Instantaneous Forward Current-Ampere
Amp Per lge

Vo lts
Instantaneous Forward Voltage -Volts
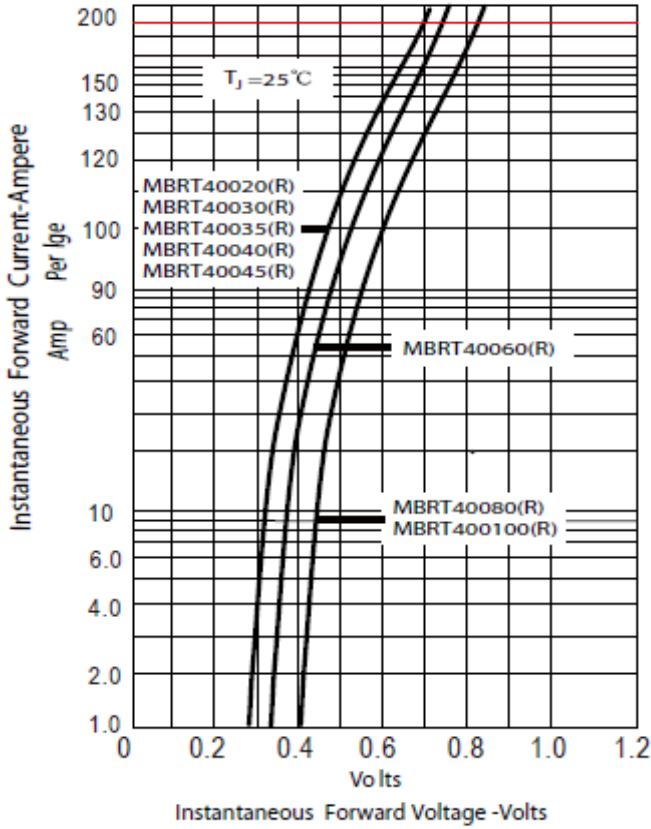
Figure.2-Forward Derating Curve

Average Forward Rectified Current-Ampere
Amp Per lge

Single Phase,Half Wave
-60Hz Res istive or Inductive Load

°C
Case Temperature - °C

Figupre.3-Peak Forward Surge Current

Peak Forward Surge Current-Ampere
Amp Per lge

8.3ms Single Half
Sine Wave
JEDEC method $T_J = 25°C$

Cycles
Number Of Cycles At60Hz -Cycles
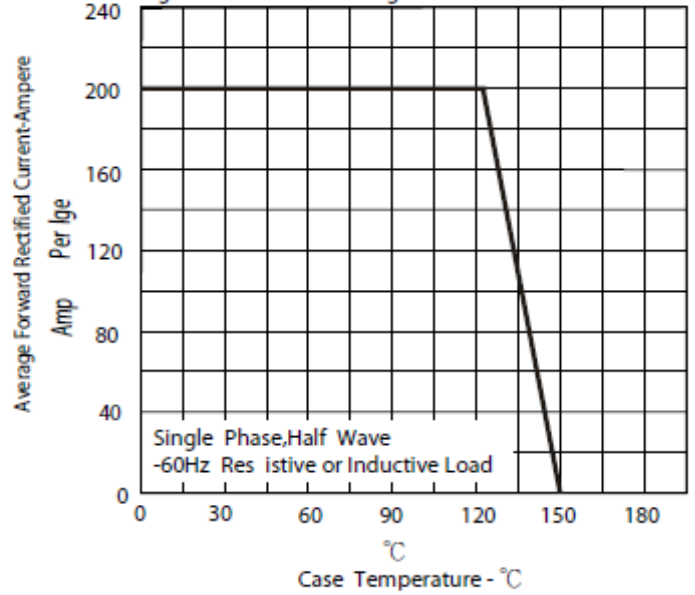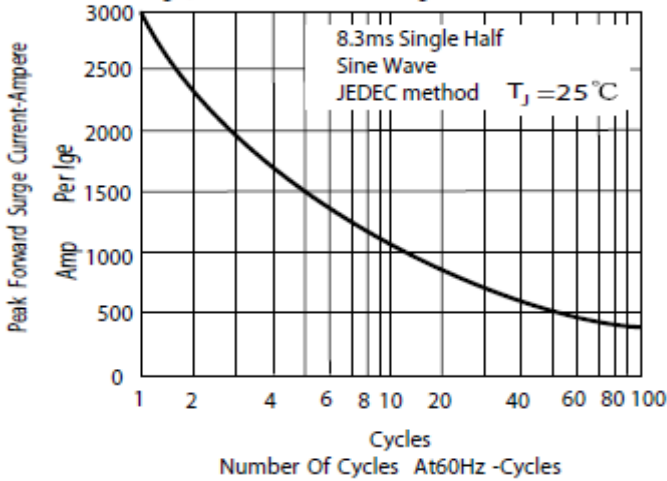
Figure.4-Typical Reverse Characteristics

Instantaneous Reverse Leakage Current- mA
mA

$T_J = 150°C$

$T_J = 100°C$

$T_J = 25°C$

Volts
Revers Voltage - Volts(%)
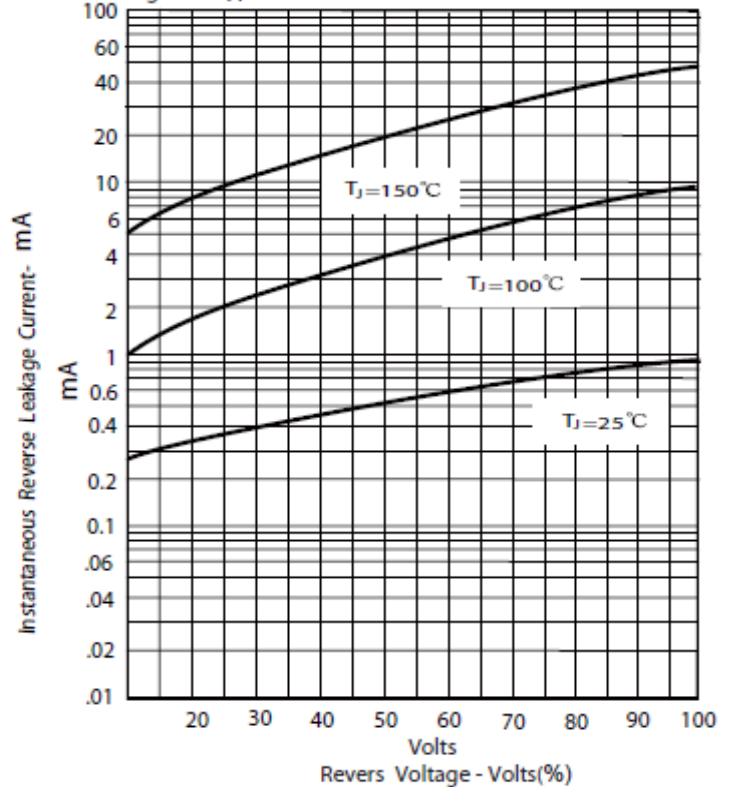
Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.
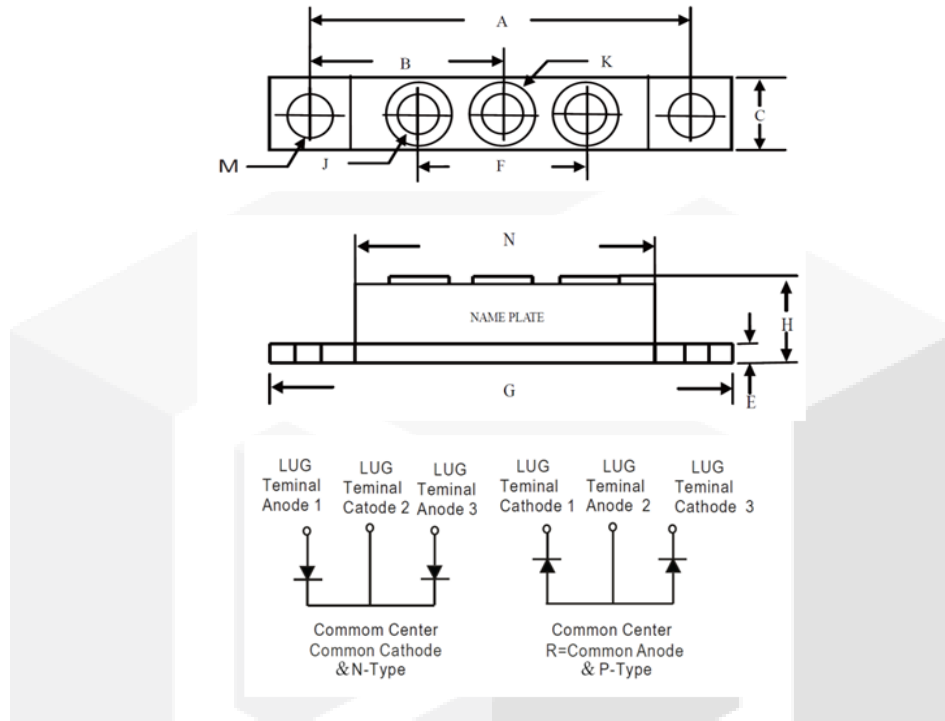
DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	3.150	NOM	80.01	NOM
B	1.565	1.585	39.75	40.26
C	0.700	0.800	17.78	20.32
E	0.119	0.132	3.02	3.35
F	1.327	-----	33.72	-----
G	3.550	3.650	90.17	92.71
H	0.677	0.720	17.20	18.30
J	1/4 -20 UNC FULL			
K	0.472	0.511	12	13
M	0.275	0.295	6.99	7.49
N	2.380	2.460	60.5	62.5

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